Intel - EP20K100CQ240C9 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	416
Number of Logic Elements/Cells	4160
Total RAM Bits	53248
Number of I/O	189
Number of Gates	263000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k100cq240c9

- Advanced interconnect structure
  - Copper interconnect for high performance
  - Four-level hierarchical FastTrack® interconnect structure providing fast, predictable interconnect delays
  - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
  - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
  - Interleaved local interconnect allows one LE to drive 29 other LEs through the fast local interconnect
- Advanced software support
  - Software design support and automatic place-and-route provided by the Altera® Quartus™ II development system for Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations
  - Altera MegaCore® functions and Altera Megafunction Partners Program (AMPP℠) megafunctions optimized for APEX 20KC architecture available
  - NativeLink™ integration with popular synthesis, simulation, and timing analysis tools
  - Quartus II SignalTap® embedded logic analyzer simplifies in-system design evaluation by giving access to internal nodes during device operation
  - Supports popular revision-control software packages including PVCS, RCS, and SCCS

Table 3. APEX 20KC QFP &BGA Package Options & I/O Count *Notes (1), (2)*

Device	144-Pin TQFP	208-Pin PQFP	240-Pin PQFP	356-Pin BGA	652-Pin BGA
EP20K100C	92	151	183	246	
EP20K200C		136	168	271	376
EP20K400C					488
EP20K600C					488
EP20K1000C					488
EP20K1500C					488

Cascade Chain

With the cascade chain, the APEX 20KC architecture can implement functions with a very wide fan-in. Adjacent LUTs can compute portions of a function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical `AND` or logical `OR` (via De Morgan's inversion) to connect the outputs of adjacent LEs. Each additional LE provides four more inputs to the effective width of a function, with a short cascade delay. Cascade chain logic can be created automatically by the Quartus II Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than ten LEs are implemented automatically by linking LABs together. For enhanced fitting, a long cascade chain skips alternate LABs in a MegaLAB structure. A cascade chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure. Figure 7 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in.

Figure 7. APEX 20KC Cascade Chain

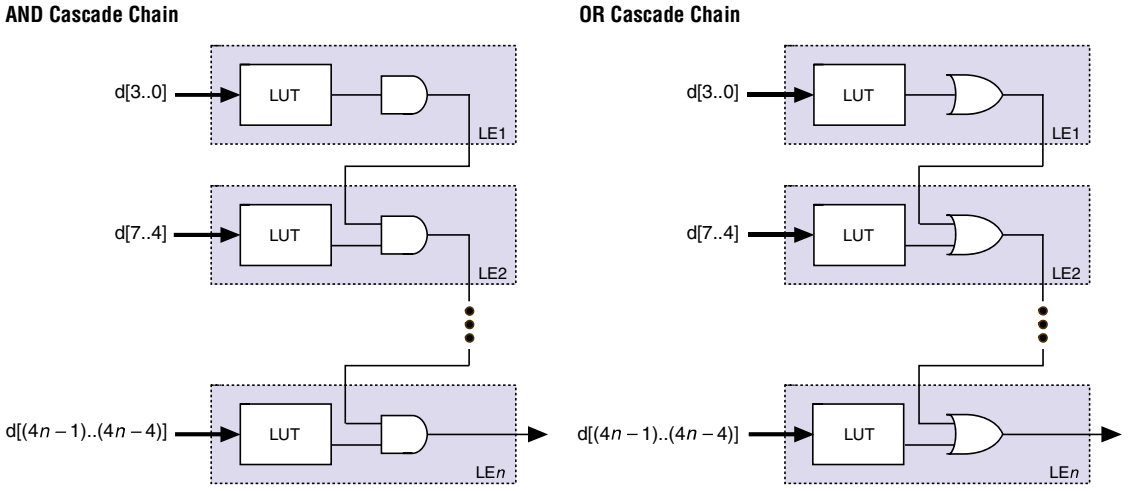


Table 8. APEX 20KC Routing Scheme

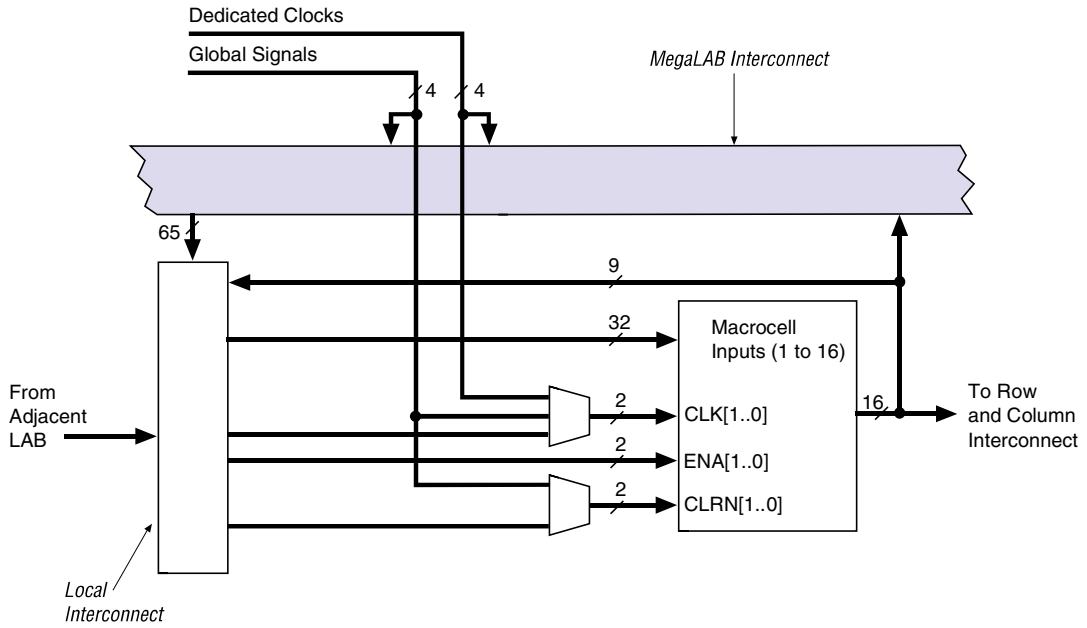
Source	Destination								
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O pin					✓	✓	✓	✓	
Column I/O pin					✓			✓	✓
LE					✓	✓	✓	✓	
ESB					✓	✓	✓	✓	
Local interconnect	✓	✓	✓	✓					
MegaLAB interconnect					✓				
Row FastTrack interconnect						✓		✓	
Column FastTrack interconnect						✓	✓		
FastRow interconnect					✓				

Product-Term Logic

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. Each ESB is fed by 32 inputs from the adjacent local interconnect; therefore, it can be driven by the MegaLAB interconnect or the adjacent LAB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

Figure 13. Product-Term Logic in ESB

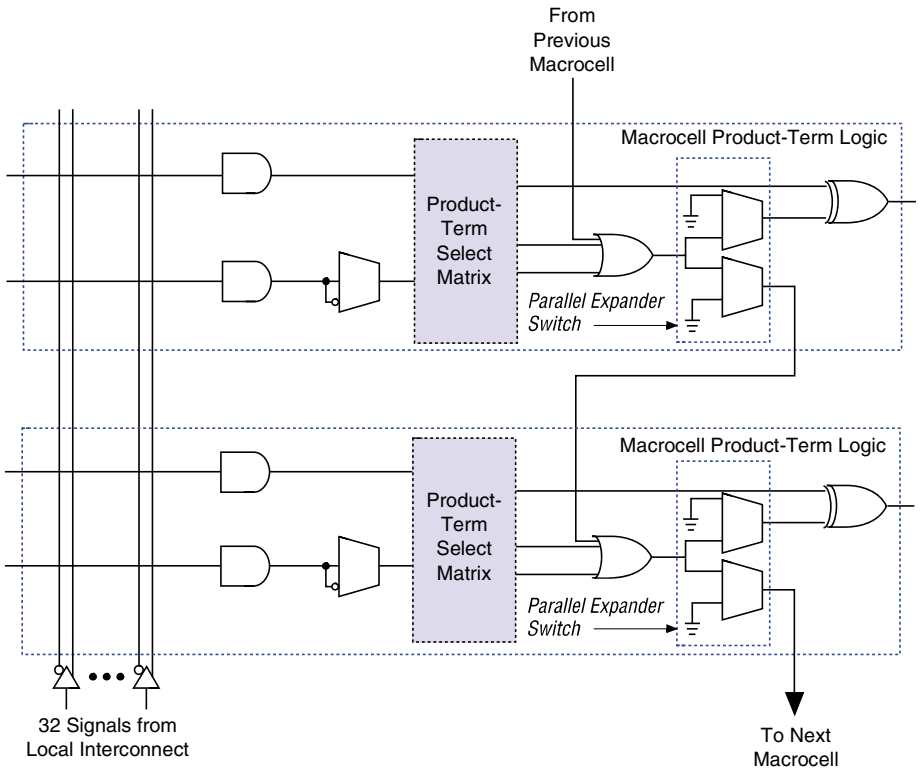


Macrocells

APEX 20KC macrocells can be configured individually for either sequential or combinatorial logic operation. The macrocell consists of three functional blocks: the logic array, the product-term select matrix, and the programmable register.

Combinatorial logic is implemented in the product terms. The product-term select matrix allocates these product terms for use as either primary logic inputs (to the OR and XOR gates) to implement combinatorial functions, or as parallel expanders to be used to increase the logic available to another macrocell. One product term can be inverted; the Quartus II software uses this feature to perform De Morgan's inversion for more efficient implementation of wide OR functions. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset. Figure 14 shows the APEX 20KC macrocell.

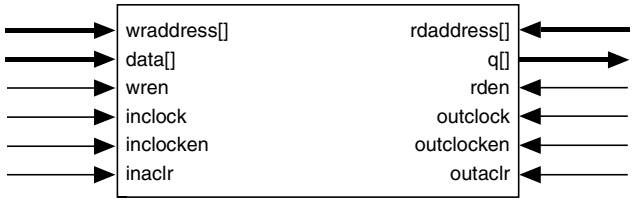
Figure 16. APEX 20KC Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

Figure 17. ESB Block Diagram



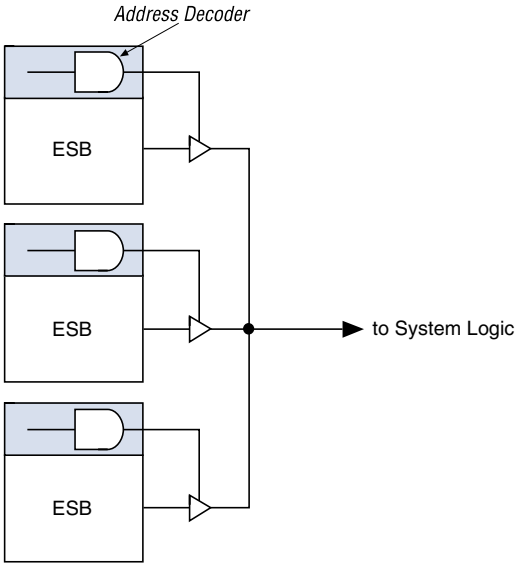
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

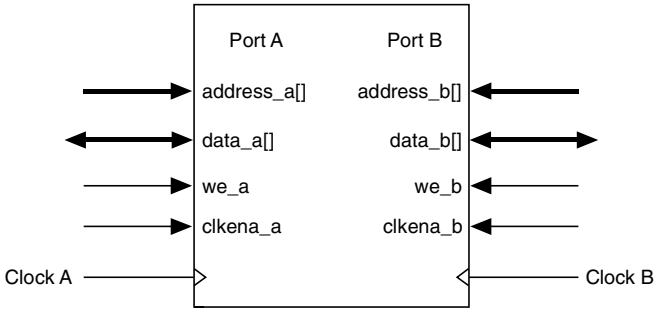
Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two ESBs are used to support two simultaneous reads or writes.

The ESB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in Figure 19.

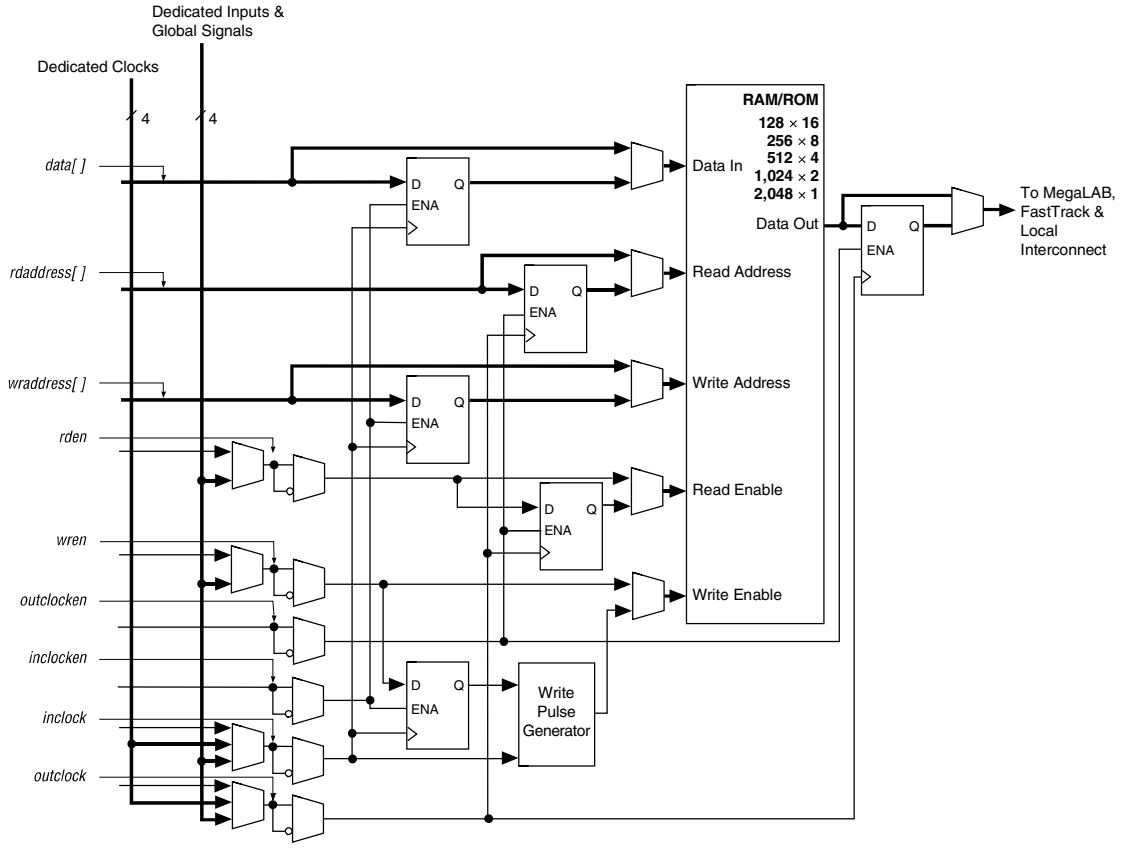
Figure 19. APEX 20KC ESB Implementing Dual-Port RAM



Read/Write Clock Mode

The read/write clock mode contains two clocks. One clock controls all registers associated with writing: data input, WE, and write address. The other clock controls all registers associated with reading: read enable (RE), read address, and data output. The ESB also supports clock enable and asynchronous clear signals; these signals also control the read and write registers independently. Read/write clock mode is commonly used for applications where reads and writes occur at different system frequencies. Figure 20 shows the ESB in read/write clock mode.

Figure 20. ESB in Read/Write Clock Mode *Note (1)*



Note:
(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.

Tables 11 and 12 summarize the ClockLock and ClockBoost parameters for APEX 20KC devices.

Table 11. APEX 20KC ClockLock & ClockBoost Parameters *Note (1)*

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_R	Input rise time				5	ns
t_F	Input fall time				5	ns
t_{INDUTY}	Input duty cycle		40		60	%
$t_{INJITTER}$	Input jitter peak-to-peak				2% of input period	%
$t_{OUTJITTER}$	RMS jitter on ClockLock or ClockBoost-generated clock				0.35% of output period	%
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		45		55	%
t_{LOCK} *(2), (3)*	Time required for ClockLock or ClockBoost to acquire lock				40	µs

Table 12. APEX 20KC Clock Input & Output Parameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	I/O Standard	-7 Speed Grade		-8 Speed Grade		Units
			Min	Max	Min	Max	
f_{VCO} *(4)*	Voltage controlled oscillator operating range		200	500	200	500	MHz
f_{CLOCK0}	Clock0 PLL output frequency for internal use		1.5	335	1.5	200	MHz
f_{CLOCK1}	Clock1 PLL output frequency for internal use		20	335	20	200	MHz
f_{CLOCK0_EXT}	Output clock frequency for external clock0 output	3.3-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		2.5-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		1.8-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		GTL+	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		LVDS	*(5)*	*(5)*	*(5)*	*(5)*	MHz

The APEX 20KC device instruction register length is 10 bits. The APEX 20KC device USERCODE register length is 32 bits. Tables 14 and 15 show the boundary-scan register length and device IDCODE information for APEX 20KC devices.

Table 14. APEX 20KC Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EP20K100C	774
EP20K200C	1,164
EP20K400C	1,506
EP20K600C	1,806
EP20K1000C	2,190
EP20K1500C	2,502

Table 15. 32-Bit APEX 20KC Device IDCODE

Device	IDCODE (32 Bits) *(1)*			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) *(2)*
EP20K100C	0000	1000 0001 0000 0000	000 0110 1110	1
EP20K200C	0000	1000 0010 0000 0000	000 0110 1110	1
EP20K400C	0000	1000 0100 0000 0000	000 0110 1110	1
EP20K600C	0000	1000 0110 0000 0000	000 0110 1110	1
EP20K1000C	0000	1001 0000 0000 0000	000 0110 1110	1
EP20K1500C	0000	1001 0101 0000 0000	000 0110 1110	1

Notes:
(1) The most significant bit (MSB) is on the left.
(2) The IDCODE's least significant bit (LSB) is always 1.

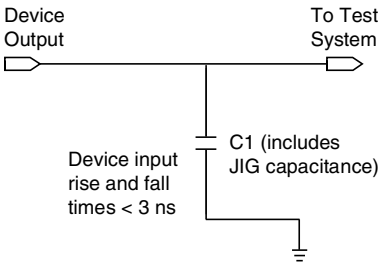
Figure 30 shows the timing requirements for the JTAG signals.

Generic Testing

Each APEX 20KC device is functionally tested. Complete testing of each configurable SRAM bit and all logic functionality ensures 100% yield. AC test measurements for APEX 20KC devices are made under conditions equivalent to those shown in Figure 31. Multiple test patterns can be used to configure devices during all stages of the production flow. AC test criteria include:

- Power supply transients can affect ACmeasurements.
- Simultaneous transitions of multiple outputs should be avoided for accurate measurement.
- Threshold tests must not be performed under AC conditions.
- Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result.

Figure 31. APEX 20KC AC Test Conditions



Operating Conditions

Tables 17 through 20 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KC devices.

Table 17. APEX 20KC Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 20. APEX 20KC Device Capacitance *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –0.5 V or overshoot to 4.6 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(6) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(7) These values are specified under the APEX 20KC device recommended operating conditions, shown in Table 18 on page 53.
(8) This value is specified for normal device operation. The value may vary during power-up.
(9) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(10) Capacitance is sample-tested only.

Tables 21 through 36 list the DC operating specifications for the supported I/O standards. These tables list minimal specifications only; APEX 20KC devices may exceed these specifications.

Table 21. LVTTL I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.8	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	I_{OH} = –12 mA, V_{CCIO} = 3.0 V *(1)*	2.4		V
V_{OL}	Low-level output voltage	I_{OL} = 12 mA, V_{CCIO} = 3.0 V *(2)*		0.4	V

Table 30. SSTL-2 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –15.2 mA *(1)*	V_{TT} + 0.76			V
V_{OL}	Low-level output voltage	I_{OL} = 15.2 mA *(2)*			V_{TT} – 0.76	V

Table 31. SSTL-3 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{TT} + 0.6			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{TT} – 0.6	V

Table 36. CTT I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF} *(3)*	Termination and reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		V_{REF} + 0.2			V
V_{IL}	Low-level input voltage				V_{REF} – 0.2	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	–10		10	µA
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{REF} + 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{REF} – 0.4	V
I_O	Output leakage current (when output is high Z)	$GND \le V_{OUT} \le V_{CCIO}$	–10		10	µA

Notes to tables:

(1) The I_{OH} parameter refers to high-level output current.
(2) The I_{OL} parameter refers to low-level output current. This parameter applies to open-drain pins as well as output pins.
(3) V_{REF} specifies center point of switching range.

Figure 32 shows the output drive characteristics of APEX 20KC devices.

Table 38. APEX 20KC f_{MAX} ESB Timing Parameters

Symbol	Parameter
t_{ESBARC}	ESB asynchronous read cycle time
t_{ESBSRC}	ESB synchronous read cycle time
t_{ESBAWC}	ESB asynchronous write cycle time
t_{ESBSWC}	ESB synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay

Table 39. APEX 20KC f_{MAX} Routing Delays

Symbol	Parameter
t_{F1-4}	Fan-out delay estimate using local interconnect
t_{F5-20}	Fan-out delay estimate using MegaLab interconnect
t_{F20+}	Fan-out delay estimate using FastTrack interconnect

Table 42. APEX 20KC External Bidirectional Timing Parameters *Note (1)*

Symbol	Parameter	Condition
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 35 pF
$t_{XZBIDIR}$	Synchronous output enable register to output buffer disable delay	C1 = 35 pF
$t_{ZXBIDIR}$	Synchronous output enable register to output buffer enable delay	C1 = 35 pF
$t_{INSUBIDIRPLL}$	Setup time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{INHBIDIRPLL}$	Hold time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{OUTCOBIDIRPLL}$	Clock-to-output delay for bidirectional pins with PLL clock at IOE register	C1 = 35 pF
$t_{XZBIDIRPLL}$	Synchronous output enable register to output buffer disable delay with PLL	C1 = 35 pF
$t_{ZXBIDIRPLL}$	Synchronous output enable register to output buffer enable delay with PLL	C1 = 35 pF

Note to tables:
(1) These timing parameters are sample-tested only.

Table 48. EP20K100C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.9						ns
$t_{INHBIDIR}$	0.0						ns
$t_{OUTCOBIDIR}$	2.0	5.0					ns
$t_{XZBIDIR}$		7.1					ns
$t_{ZXBIDIR}$		7.1					ns
$t_{INSUBIDIRPLL}$	3.9						ns
$t_{INHBIDIRPLL}$	0.0						ns
$t_{OUTCOBIDIRPLL}$	0.5	2.1					ns
$t_{XZBIDIRPLL}$		4.2					ns
$t_{ZXBIDIRPLL}$		4.2					ns

Table 49. EP20K200C f_{MAX} LE Timing Parameters Note (1)

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.3						ns
t_{H}	0.3						ns
t_{CO}		0.3					ns
t_{LUT}		0.7					ns

Table 60. EP20K400C External Bidirectional Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.4						ns
$t_{INHBIDIR}$	0.0						ns
$t_{OUTCOBIDIR}$	2.0	5.0					ns
$t_{XZBIDIR}$		7.1					ns
$t_{ZXBIDIR}$		7.1					ns
$t_{INSUBIDIRPLL}$	3.8						ns
$t_{INHBIDIRPLL}$	0.0						ns
$t_{OUTCOBIDIRPLL}$	0.5	2.1					ns
$t_{XZBIDIRPLL}$		4.2					ns
$t_{ZXBIDIRPLL}$		4.2					ns

Table 61. EP20K600C f_{MAX} LE Timing Parameters Note (1)

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.3						ns
t_{H}	0.3						ns
t_{CO}		0.3					ns
t_{LUT}		0.7					ns

Table 79. Selectable I/O Standard Input Delays

Symbol	-7 Speed Grade		-8 Speed Grade (1)		-9 Speed Grade (1)		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.0					ns
LVTTL		0.0					ns
2.5 V		0.1					ns
1.8 V		0.5					ns
PCI		0.4					ns
GTL+		–0.3					ns
SSTL-3 Class I		–0.4					ns
SSTL-3 Class II		–0.4					ns
SSTL-2 Class I		–0.3					ns
SSTL-2 Class II		–0.3					ns
LVDS		–0.2					ns
CTT		–0.3					ns
AGP		0.0					ns

Table 80. Selectable I/O Standard Output Delays

Symbol	-7 Speed Grade		-8 Speed Grade (1)		-9 Speed Grade (1)		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.0					ns
LVTTL		0.0					ns
2.5 V		0.5					ns
1.8 V		1.7					ns
PCI		–0.2					ns
GTL+		–0.4					ns
SSTL-3 Class I		–0.1					ns
SSTL-3 Class II		–0.6					ns
SSTL-2 Class I		0.0					ns
SSTL-2 Class II		–0.4					ns
LVDS		–0.8					ns
CTT		–0.2					ns
AGP		–0.4					ns

Note to tables:
(1) Timing information will be released in a future version of this data sheet.

Multiple APEX 20KC devices can be configured in any of five configuration schemes by connecting the configuration enable (nCE) and configuration enable output (nCEO) pins on each device.

Table 81. Data Sources for Configuration

Configuration Scheme	Data Source
Configuration device	EPC16, EPC2, or EPC1 configuration device
Passive serial (PS)	MasterBlaster or ByteBlasterMV download cable or serial data source
Passive parallel asynchronous (PPA)	Parallel data source
Passive parallel synchronous (PPS)	Parallel data source
JTAG	MasterBlaster or ByteBlasterMV download cable or a microprocessor with a Jam Standard Test and Programming Language (STAPL) or JBC File

For more information on configuration, see *Application Note 116 (Configuring APEX 20K, FLEX 10K & FLEX 6000 Devices.)*

Device Pin-Outs

See the Altera web site **(http://www.altera.com)** or the ***Altera Digital Library*** for pin-out information.

Revision History

The information contained in the *APEX 20KC Programmable Logic Device Data Sheet* version 1.1 supersedes information published in pervious versions.

The following changes were made to the *APEX 20KC Programmable Logic Device Data Sheet* version 1.1: updated maximum user I/O pins in Table 1.